

1. SCOPE

This specification provide the ratings and the requirements for high voltage silicon diode ESJA57-04A

2. OUT VIEW

Shape and dimensions are described

3. IDENTIFICATION

The diode shall be marked with Cathode Mark

4. RATINGS AND CHARACTERISTICS

4.1 ABSOLUTE MAX. RATINGS. ( Ta=25 °C unless otherwise noted. )

Items	Conditions	Symbols	Ratings	Units
Repetitive peak reverse voltage.		V <sub>RRM</sub>	4	kVpeak
Non-Repetitive peak forward current.	50Hz Sine-half wave peak value	I <sub>FSM</sub>	0.5	Apeak
Average forward current.	50Hz Sine Wave	I <sub>AV</sub>	5	mA
Allowable junction temperature.		T <sub>j</sub>	120	°C
Storage temperature range.		T <sub>stg</sub>	-40-120	°C
Allowable operating case temperature.		T <sub>c</sub>	100	°C

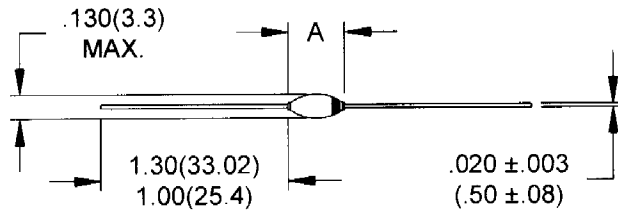
4.2 ELECTRICAL CHARACTERISTICS ( Ta=25 °C unless otherwise noted. )

Items	Conditions	Symbols	Ratings	Units
Maximum forward voltage drop	I <sub>F</sub> =10mA	V <sub>F</sub>	15	V
Maximum reverse current	V <sub>R</sub> = 4kV	I <sub>R1</sub>	2	μA
Maximum reverse current	V <sub>R</sub> = 4kV, 100°C	I <sub>R2</sub>	5	μA
Maximum reverse recovery time	I <sub>F</sub> =2mA, I <sub>R</sub> =4mA	t <sub>rr</sub>	0.08	μS
Maximum junction capacitance	f=1MHz, V <sub>R</sub> =0V	C <sub>j</sub>	2	pF

4.3 MECHANICAL CHARACTERISTICS

Weight : Ca. 0.2 gr.  
 Vibration proof : 5 G





A
$.300(7.62)$ MAX.
$.350(8.89)$ MAX.